



USJ60R280Z

Power MOSFET

18A, 600V N-CHANNEL SUPER-JUNCTION MOSFET

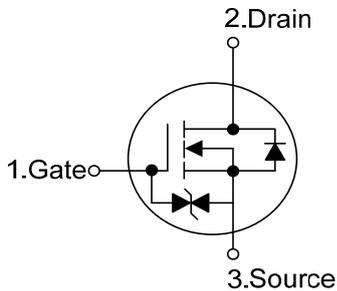
■ DESCRIPTION

The **UTC USJ60R280Z** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

- * $R_{DS(ON)} \leq 0.28 \Omega @ V_{GS}=10V, I_D=3.8A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness
- * With ESD protection

■ SYMBOL

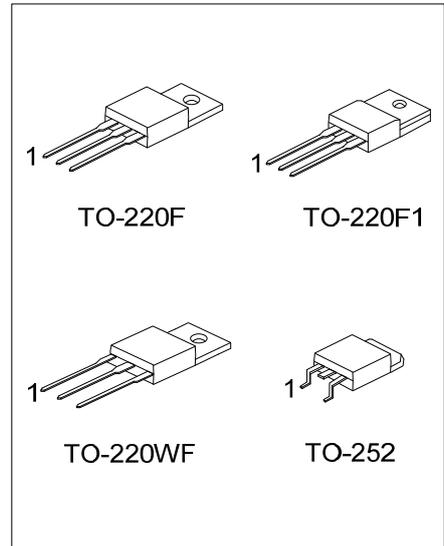


■ ORDERING INFORMATION

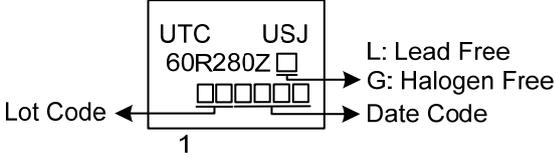
| Ordering Number | | Package | Pin Assignment | | | Packing |
|-------------------|-------------------|----------|----------------|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| USJ60R280ZL-TF1-T | USJ60R280ZG-TF1-T | TO-220F1 | G | D | S | Tube |
| USJ60R280ZL-TF3-T | USJ60R280ZG-TF3-T | TO-220F | G | D | S | Tube |
| USJ60R280ZL-TW1-T | USJ60R280ZG-TW1-T | TO-220WF | G | D | S | Tube |
| USJ60R280ZL-TN3-R | USJ60R280ZG-TN3-R | TO-252 | G | D | S | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------|
| <p>USJ60R280ZG-TF1-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p> | <p>(1) T: Tube, R: Tape Reel</p> <p>(2) TF3: TO-220F, TF1: TO-220F1, TW1: TO-220WF TN3: TO-252</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p> |
|------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------|



MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_c=25°C, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|------------------------------------|------------------------|------------------|------------|------|
| Drain-Source Voltage | | V _{DSS} | 600 | V |
| Gate-Source Voltage | | V _{GSS} | ±30 | V |
| Drain Current | Continuous | I _D | 18 | A |
| | Pulsed (Note 2) | I _{DM} | 54 | A |
| Avalanche energy | Single Pulsed (Note 3) | E _{AS} | 185 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 0.9 | V/nS |
| Power Dissipation | TO-220F/TO-220F1 | P _D | 30 | W |
| | TO-220WF | | | |
| | TO-252 | | 61 | W |
| Junction Temperature | | T _J | +150 | °C |
| Storage Temperature Range | | T _{STG} | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 100mH, I_{AS} = 1.9A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C

4. I_{SD} ≤ 18A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---------------------|------------------|-----------------|-------------|------|
| Junction to Ambient | TO-220F/TO-220F1 | θ _{JA} | 62.5 | °C/W |
| | TO-220WF | | | |
| | TO-252 | | 110 | °C/W |
| Junction to Case | TO-220F/TO-220F1 | θ _{JC} | 4.16 | °C/W |
| | TO-220WF | | | |
| | TO-252 | | 2.04 (Note) | °C/W |

Note: Device mounted on FR-4 substrate P_c board, 2oz copper, with 1inch square copper plate.

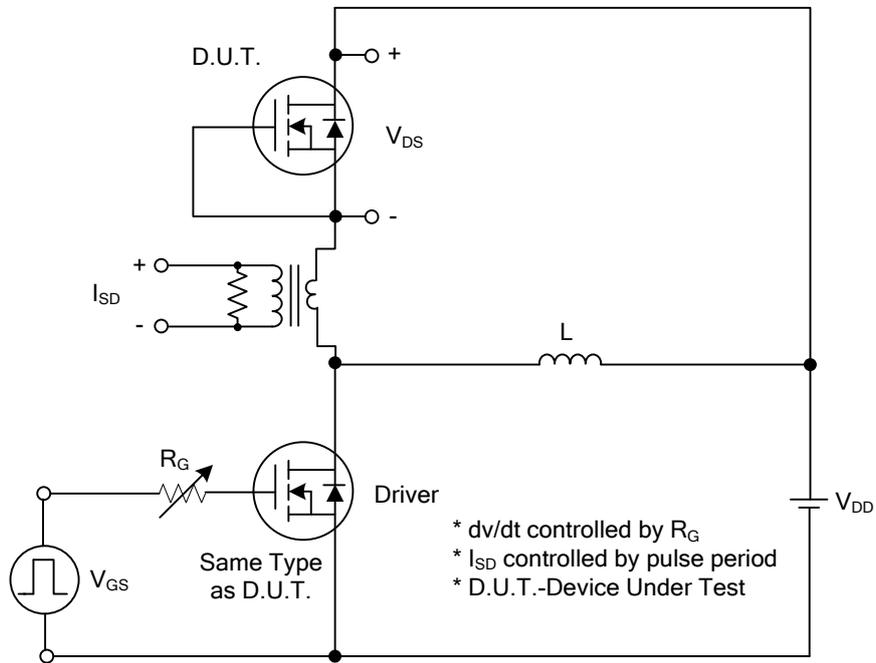
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT | |
|--------------------------------------------------------|---------|---------------------|------------------------------------------------------------------------------------------------------|-----|-----|------|------|----|
| OFF CHARACTERISTICS | | | | | | | | |
| Drain-Source Breakdown Voltage | | BV _{DSS} | V _{GS} =0V, I _D =250μA | 600 | | | V | |
| Drain-Source Leakage Current | | I _{DSS} | V _{DS} =600V, V _{GS} =0V | | | 1 | μA | |
| Gate-Source Leakage Current | Forward | I _{GSS} | V _{DS} =0V, V _{GS} =+25V | | | +10 | μA | |
| | Reverse | | V _{DS} =0V, V _{GS} =-20V | | | -10 | μA | |
| ON CHARACTERISTICS | | | | | | | | |
| Gate Threshold Voltage | | V _{GS(TH)} | V _{DS} = V _{GS} , I _D =250μA | 2.5 | | 4.5 | V | |
| Drain-Source On-State Resistance | | R _{DS(ON)} | V _{GS} =10V, I _D =3.8A | | | 0.28 | Ω | |
| DYNAMIC PARAMETERS | | | | | | | | |
| Input Capacitance | | C _{ISS} | V _{GS} =0V, V _{DS} =50V, f=1.0MHz | | 958 | | pF | |
| Output Capacitance | | C _{OSS} | | | | 831 | | pF |
| Reverse Transfer Capacitance | | C _{RSS} | | | | 61 | | pF |
| SWITCHING PARAMETERS | | | | | | | | |
| Total Gate Charge (Note 1) | | Q _G | V _{DS} =480V, V _{GS} =10V, I _D =18A (Note 1, 2) | | 38 | | nC | |
| Gate to Source Charge | | Q _{GS} | | | | 10 | | nC |
| Gate to Drain Charge | | Q _{GD} | | | | 15 | | nC |
| Turn-on Delay Time (Note 1) | | t _{D(ON)} | V _{DD} =100V, V _{GS} =10V, I _D =18A, R _G =25Ω (Note 1, 2) | | 23 | | ns | |
| Rise Time | | t _R | | | | 23 | | ns |
| Turn-off Delay Time | | t _{D(OFF)} | | | | 101 | | ns |
| Fall-Time | | t _F | | | | 30 | | ns |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | | | |
| Maximum Body-Diode Pulsed Current | | I _S | | | | 18 | A | |
| Drain-Source Diode Forward Voltage (Note 1) | | I _{SM} | | | | 54 | A | |
| Maximum Body-Diode Continuous Current | | V _{SD} | I _S =18A, V _{GS} =0V | | | 1.5 | V | |
| Reverse Recovery Time (Note 1) | | t _{rr} | I _S =18A, V _{GS} =0V, dI _F /dt=100A/μs | | 380 | | ns | |
| Reverse Recovery Charge | | Q _{rr} | | | | 5.3 | | μC |

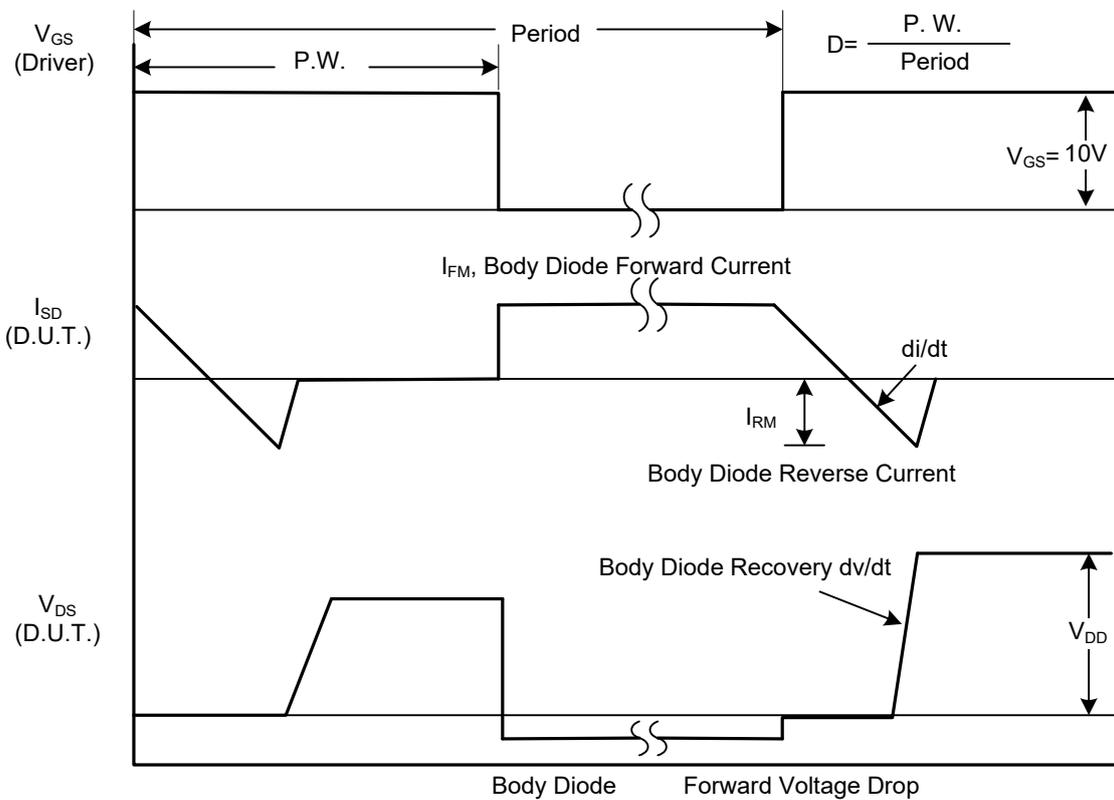
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

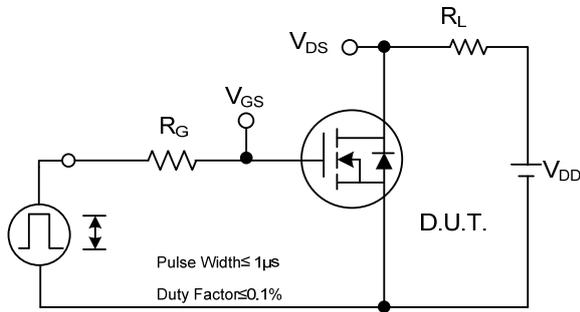


Peak Diode Recovery dv/dt Test Circuit

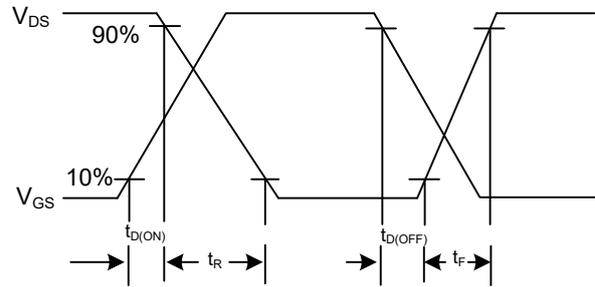


Peak Diode Recovery dv/dt Waveforms

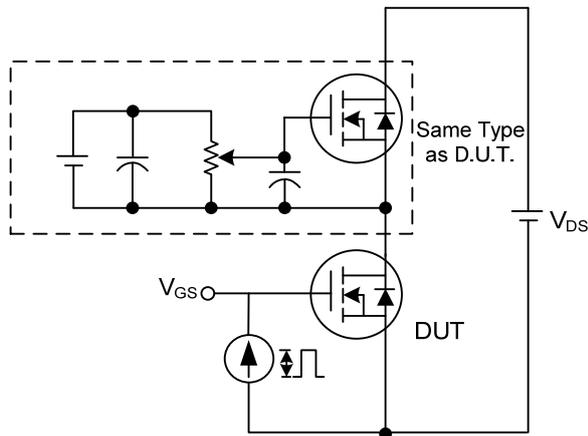
TEST CIRCUITS AND WAVEFORMS



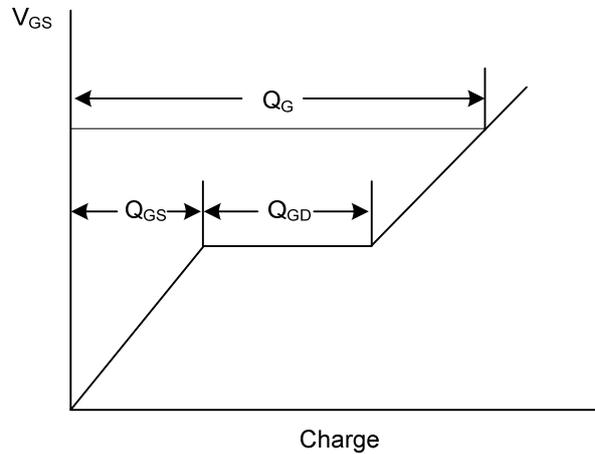
Switching Test Circuit



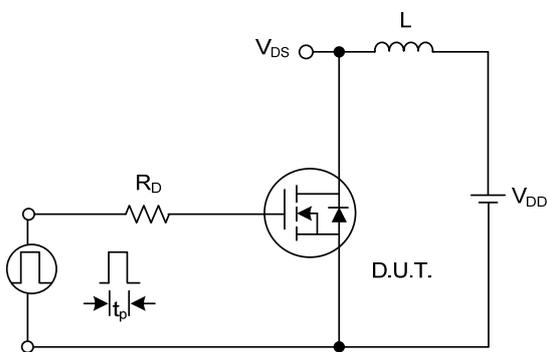
Switching Waveforms



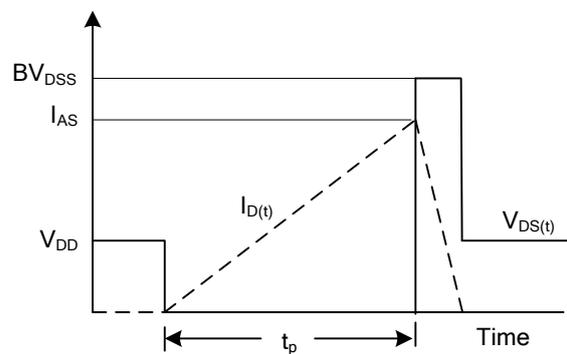
Gate Charge Test Circuit



Gate Charge Waveform

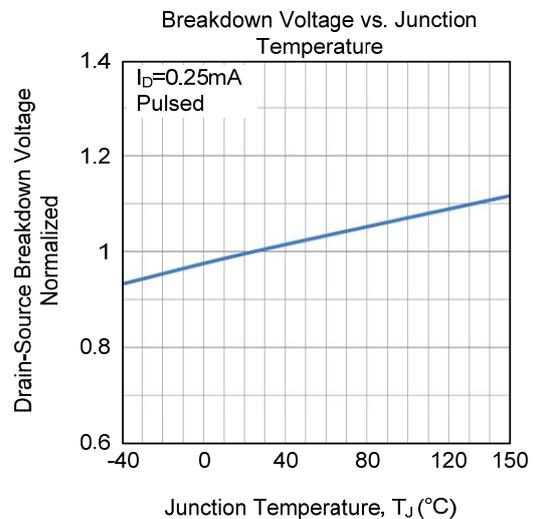
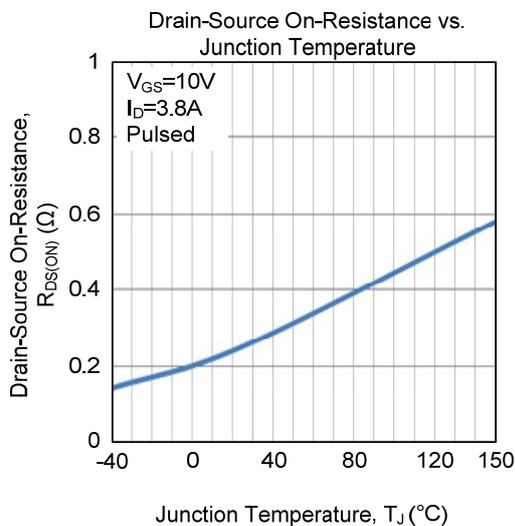
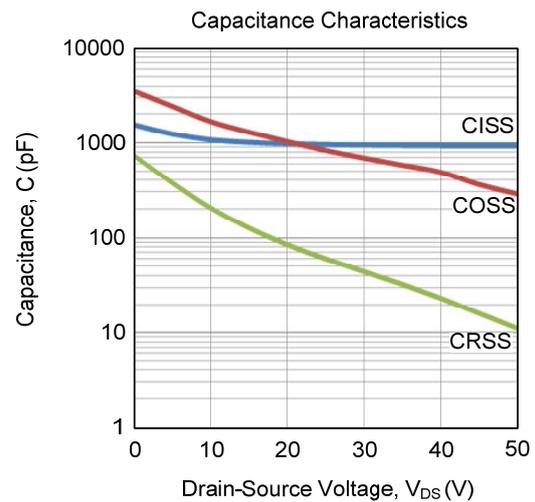
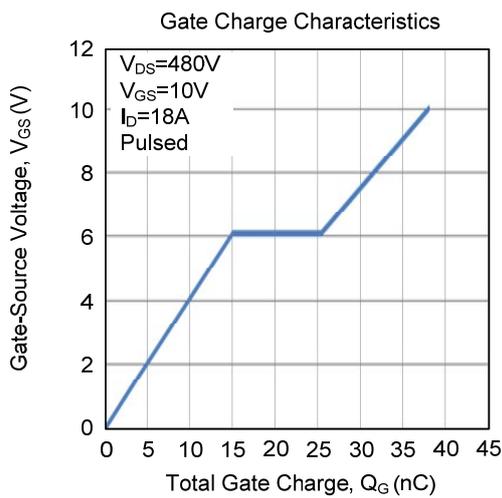
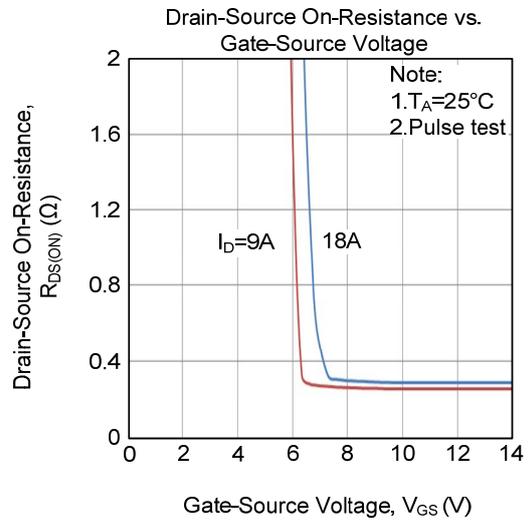
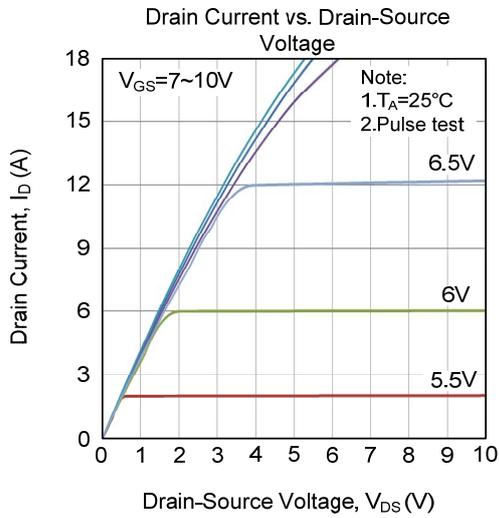


Unclamped Inductive Switching Test Circuit

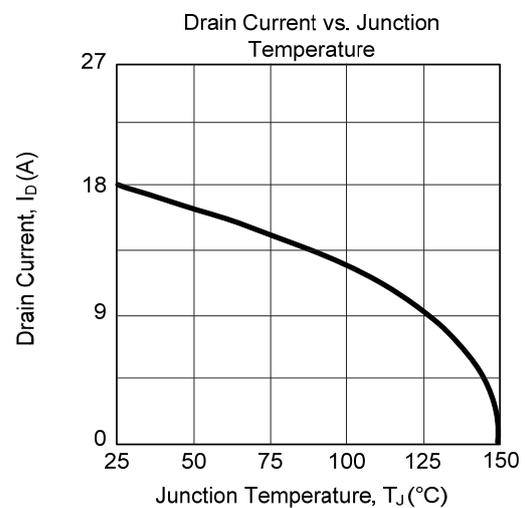
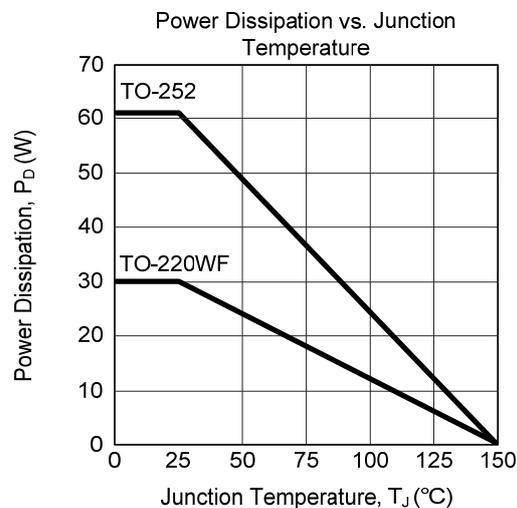
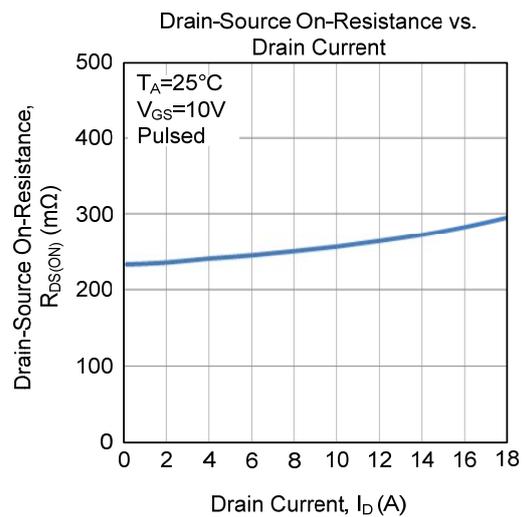
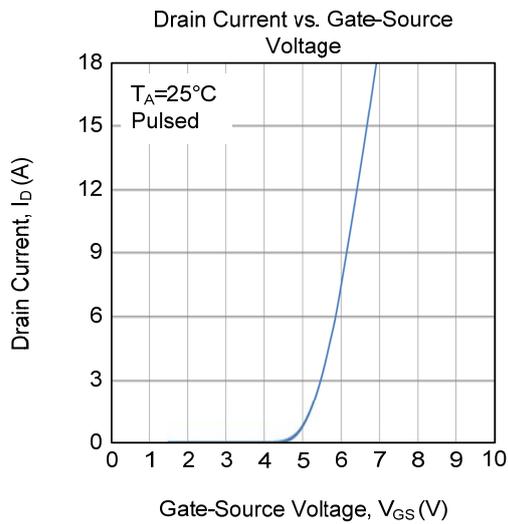
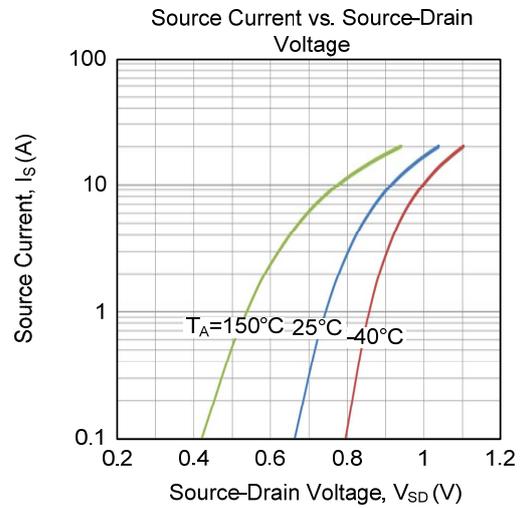
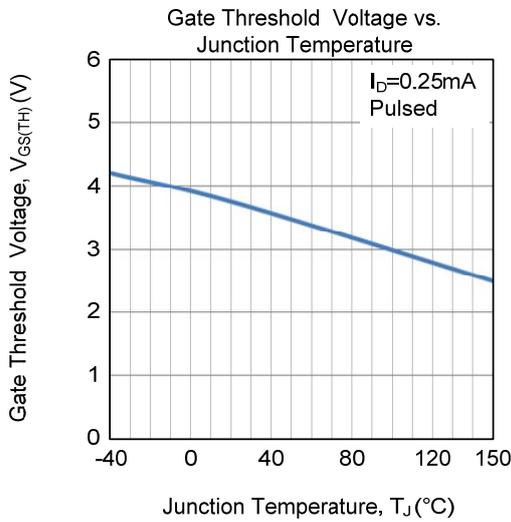


Unclamped Inductive Switching Waveforms

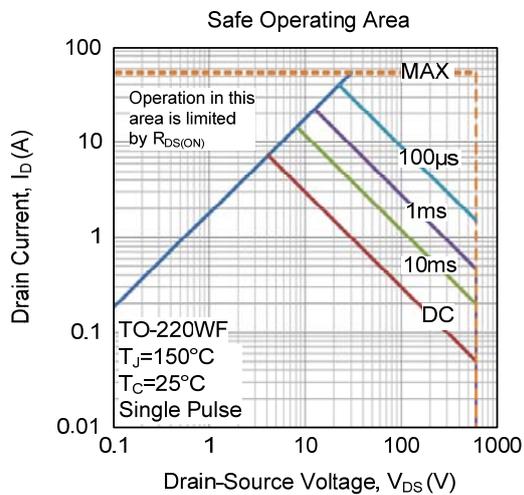
TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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